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Corrigendum: High-performance n-type black phosphorus transistors with type control via thickness and contact-metal engineering

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In Fig. 3 of this article, there are a number of errors in the colours used for the data points and curves. In Fig. 3b, the blue data should be green, referring to a thickness of '3.5 nm', and the green data should be blue, referring to a thickness of '8 nm'. In Fig. 3d, the blue data should be green and refer to a thickness of '3.5 nm', the green data should be blue and refer to a thickness of '8 nm' and the orange data should refer to a thickness of '13 nm'.

In Table 1, the Pd contacts on 13–14.5 nm of BP were 'Unipolar p-type', not 'Unipolar n-type'.

The correct version of Fig. 3 and Table 1 appear below.

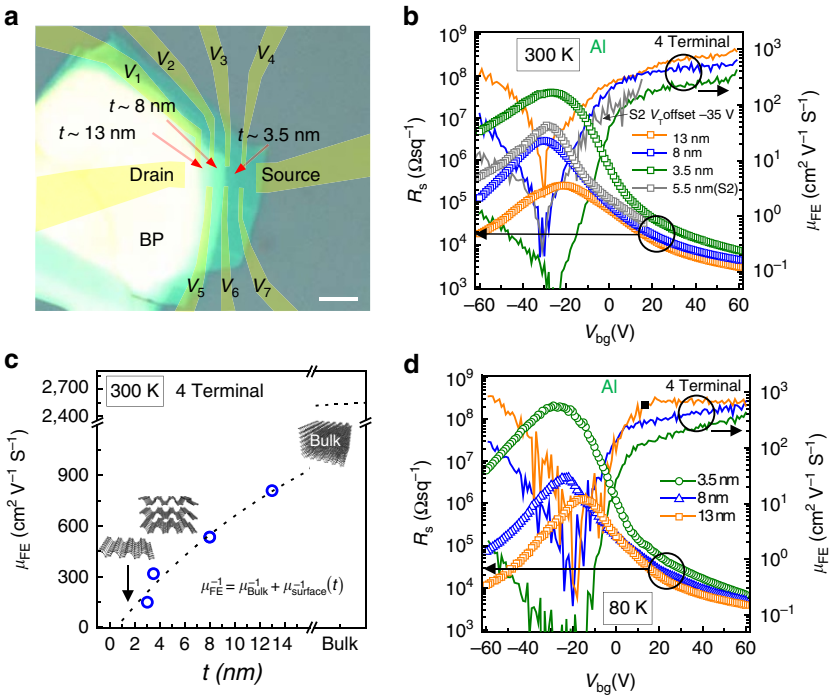

Figure 3

Table 1 | Type control summary by thickness and contact metal.

	BP thickness		
	2.5–5.5 nm	**7–8 nm**	**13–14.5 nm**
Al contacts	Unipolar n-type	Unipolar n-type	Ambipolar
Pd contacts	Ambipolar	Ambipolar p-type dominant	Unipolar p-type